



2829

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April 30, 2003

Box: Non-Fee Amendment Commissioner For Patents Washington, D.C. 20231

Re:

Applicant(s):

Michael R. Krames; Tetsuya Takeuchi; Norihide Yamada; Hiroshi

Amano; Isamu Akasaki

Assignee:

Lumileds Lighting U.S., LLC

Title:

Nitride Semiconductor Device With Reduced Polarization Fields

Serial No.:

09/992,192

Examiner:

Maria F. Guerrero

Filed: November 13, 2001

Group Art Unit: 2822

Docket No.:

M-11040-3P US

Dear Sir:

EV 342554919 US

Transmitted herewith are the following documents in the above-identified application:

- (1) This Transmittal Letter (1 page);
- (2) Response to Office Action (9 pages).

No additional fee is required.

The fee has been calculated as

The fee has been calculated as shown below:

		Claims Remainin	_	Highest No. Previously Paid For		Present Extra		Rate		Additional <u>Fee</u>	
Total	Claims	18	Minus	23	=	0	x	\$18	\$	0.00	
Indep Clain	endent	3	Minus	4	=	0	х	\$84	\$	0.00	
	Fee of for the first filing of one or more multiple \$ dependent claims per application \$									•	
\boxtimes	Conditional Petition for Extension of Time: If an extension of time is required for timely filing of the enclosed document(s) after all papers filed with this transmittal have been considered, an extension of time is hereby requested.										
	Please charge our Deposit Account No. 502226 in the amount of 0.00										
\boxtimes	Also, charge any additional fees required and credit any overpayment to our Deposit Account No. 502226.										
							1	otal:	\$	0.00	
EXPRESS MAIL LABEL NO:					Respectfully submitted,						

Respectfully submitted,

Rachel V. Leiterman

Attorney for Applicant(s)

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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San Jose, California April 30, 2003

COMMISSIONER FOR PATENTS

Washington, D. C. 20231

RESPONSE TO OFFICE ACTION

Dear Sir:

This responds to the Office Action dated January 31, 2003. Please amend the above-identified application as follows.

IN THE CLAIMS

No claims are amended in this submission. The claims are reproduced below for the Examiner's convenience.

1. A method for fabricating a light-emitting semiconductor device including a III-Nitride quantum well layer, said method comprising:

selecting a facet orientation of said III-Nitride quantum well layer to control a field strength of a piezoelectric field therein; and

growing said III-Nitride quantum well layer with said selected facet orientation.

2. The method of Claim 1, further comprising selecting said facet orientation to reduce a magnitude of an electric field strength in said quantum well layer.

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